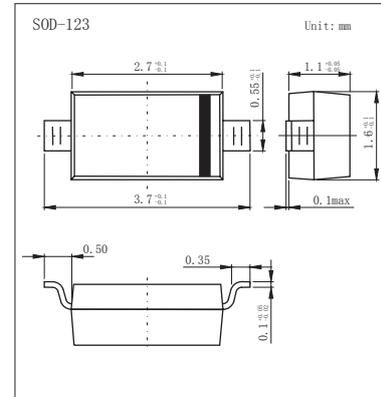


Schottky Diodes

BAT46W (KAT46W)



■ Features

- High Breakdown Voltage
- Low Turn-on Voltage
- Guard Ring Construction for Transient Protection

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Current	I_F	150	mA
Peak Forward Surge Current @ $t_p < 1.0\text{s}$, Duty Cycle < 50% (Note.1)	I_{FM}	350	
Forward Surge Forward Current @ $t_p=10\text{ms}$ (Note.1)	I_{FSM}	750	
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	420	$^\circ\text{C/W}$
		370	
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1: Part mounted on FR-4 board with recommended pad layout

Note.2: Part mounted on Polyimide board with recommended pad layout

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu\text{A}$	100			V
Forward voltage	V_F	$I_F = 0.1 \text{ mA}$			0.25	
		$I_F = 10 \text{ mA}$			0.45	
		$I_F = 250 \text{ mA}$			1	
Reverse voltage leakage current	I_{R1}	$V_R = 1.5 \text{ V}$			0.3	μA
	I_{R2}	$V_R = 10 \text{ V}$			0.5	
	I_{R3}	$V_R = 50 \text{ V}$			1	
	I_{R4}	$V_R = 75 \text{ V}$			2	
Total capacitance	C_T	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$		20		pF
		$V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$		12		

■ Marking

Marking	S110
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Schottky Diodes

BAT46W (KAT46W)

■ Typical Characteristics

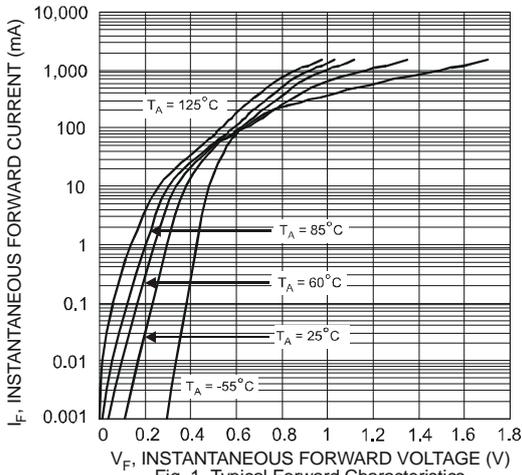


Fig. 1 Typical Forward Characteristics

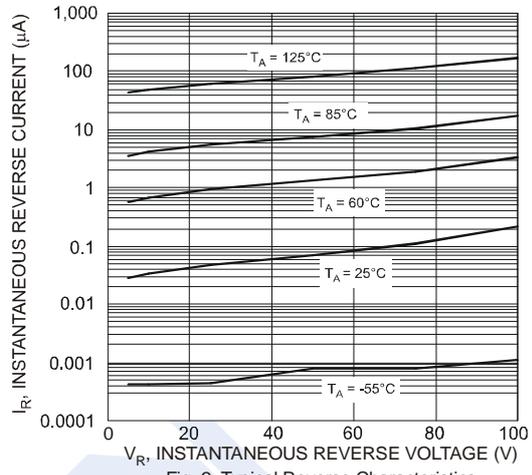


Fig. 2 Typical Reverse Characteristics

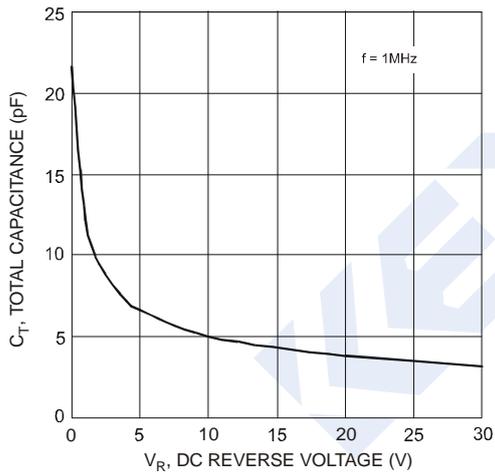


Fig. 3 Total Capacitance vs. Reverse Voltage

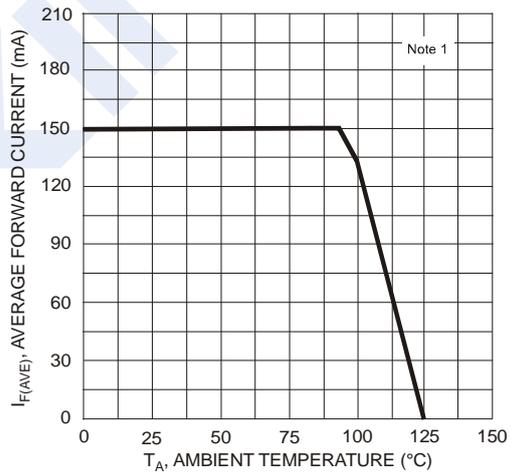


Fig. 4 Forward Current Derating

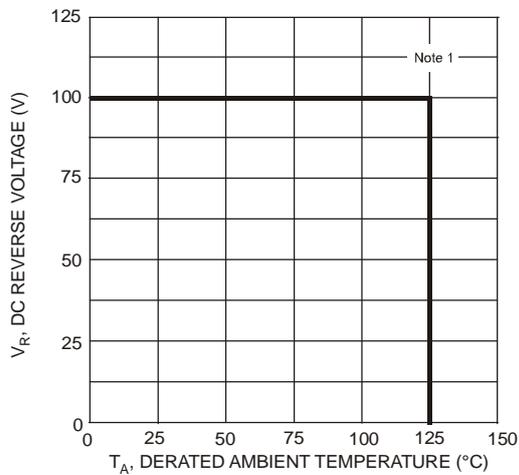


Fig. 5 Operating Temperature Derating